

CATHODE MOUNTING FOR ION SOURCE WITH INDIRECTLY HEATED CATHODE**ABSTRACT**

5 An ion source (12) embodying the present invention is for use in an ion implanter (10). The ion source comprises a gas confinement chamber (76) having conductive chamber walls (130a, 130b, 130c, 130d, 130e, 132) that bound a gas ionization zone (R). The gas confinement chamber includes an exit opening (78) to allow ions to exit the chamber. A base (80, 82, 120) positions the gas confinement chamber relative to structure (90, 14) for forming an ion beam (20) from ions exiting the gas confinement chamber.

(Fig.1)